L Number	Hits	Search Text	DB	Time stamp
1	9	ma-ching-tienin. chen-tsung-chuanin.	USPAT;	2004/07/20 11:49
		hsu-shew-tsuin.	US-PGPUB;	
			EPO; JPO;	
	450456		DERWENT	
2	452476	resist photoresist photo-resist	USPAT;	2004/07/20 11:50
			US-PGPUB;	i .
			EPO; JPO; DERWENT	
3	339939	photosensitive photo-sensitive (sensitive	USPAT;	2004/07/20 11:50
		near (photo light energy radiation))	US-PGPUB;	2004/07/20 11:50
		The transfer of the transfer o	EPO; JPO;	
			DERWENT	
4	9231	duv! (deep adj2 (uv ultraviolet ultra-violet	USPAT;	2004/07/20 11:50
		ultra adj violet))	US-PGPUB;	
		•	EPO; JPO;	
_			DERWENT	
5	116798	krf arf f2 "f.sub.2"	USPAT;	2004/07/20 11:50
			US-PGPUB;	
			EPO; JPO;	1
6	12147	("157" "193" "248") near (nm! nanometer	DERWENT	2004/07/20 33 53
"	1214/	nano-meter nano adj meter)	USPAT; US-PGPUB;	2004/07/20 11:51
	ŀ	income mano daj meterj	EPO; JPO;	
			DERWENT	
7	275665	(oxide dioxide) near (layer film coating)	USPAT;	2004/07/20 11:51
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
8	21899	etchstop etch-stop etch adj stop hardmask	USPAT;	2004/07/20 11:51
		hard-mask hard adj mask	US-PGPUB;	
			EPO; JPO;	
9	1866544	gi giligon gi gontoinĝo giligon gontoinĝo	DERWENT	0001/00/00 11
9	1000544	si silicon si-contain\$3 silicon-contain\$3	USPAT;	2004/07/20 11:51
			US-PGPUB; EPO; JPO;	
			DERWENT	
10	232413	(silicon adj (nitride oxynitride oxy-nitride	USPAT;	2004/07/20 11:51
		oxy adj nitride carbide)) "si.sub.3 n.sub.4"	US-PGPUB;	3352, 53, 25 22.32
		sion sic	EPO; JPO;	
			DERWENT	
11	7658	(430/311,313,314,317,327,328,330.ccls.	USPAT;	2004/07/20 11:51
		328/694.ccls.)	US-PGPUB;	
			EPO; JPO;	
13	68211	aspect adj ratio	DERWENT	2004/07/00 11 50
	00211	aspect adj facto	USPAT; US-PGPUB;	2004/07/20 11:52
			EPO; JPO;	
			DERWENT	
14	2549112	via contact adj hole	USPAT;	2004/07/20 11:53
			US-PGPUB;	
		,	EPO; JPO;	
15	9000	(otabaton otab atam atah add ayar a	DERWENT	
12	9000	(etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon	USPAT;	2004/07/20 11:54
		si-contain\$3 silicon-contain\$3 ) ((silicon	US-PGPUB;	
		adj (nitride oxynitride oxy-nitride oxy adj	EPO; JPO; DERWENT	
		nitride carbide)) "si.sub.3 n.sub.4" sion	DEVARIAT	
		sic ))		
16	7988	((resist photoresist photo-resist )	USPAT;	2004/07/20 11:54
		(photosensitive photo-sensitive (sensitive	US-PGPUB;	
		near (photo light energy radiation)))) with	EPO; JPO;	
		((duv! (deep adj2 (uv ultraviolet	DERWENT	
		ultra-violet ultra adj violet))) (krf arf		
		f2 "f.sub.2" ) (("157" "193" "248") near		
20	66778	<pre>(nm! nanometer nano-meter nano adj meter) )) (cur\$3 near2 (uv ultraviolet ultra-violet</pre>	HCDAM	2004/07/22
	50775	ultra adj violet (duv! (deep adj2 (uv	USPAT; US-PGPUB;	2004/07/20 12:02
		ultraviolet ultra-violet ultra adj violet))	EPO; JPO;	
		) light radiation)) photo-cur\$3 photocur\$3	DERWENT	

21	2396	((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) near4 ((cur\$3 near2 (uv ultraviolet ultra-violet ultra adj violet (duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet)) ) light radiation)) photo-cur\$3 photocur\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:03
22	4	(((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) near4 ((cur\$3 near2 (uv ultraviolet ultra-violet ultra adj violet (duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet)) ) light radiation)) photo-cur\$3 photocur\$3)) same ((oxide dioxide) near (layer film coating) ) same ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon si-contain\$3 silicon-contain\$3 ) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic )))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:11
23	1051	<pre>((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) same ((oxide dioxide) near (layer film coating)) same ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon si-contain\$3 silicon-contain\$3 ) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic )))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:12
24	34	(((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) same ((oxide dioxide) near (layer film coating)) same ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon si-contain\$3 silicon-contain\$3 ) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic )))) and ((duv! (deep adj2 (uv ultraviolet ultra-violet ultra adj violet)) ) (krf arf f2 "f.sub.2") (("157" "193" "248") near (nm! nanometer nano-meter nano adj meter) )) and (aspect adj ratio)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:20
25	5585	(aspect adj ratio) with (via contact adj hole)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:21
27	948	((aspect adj ratio) with (via contact adj hole)) with ("8" "9" "10" "11" "12" "13" "14" "15" "20")	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:26
29	1734	((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:27
30	1	<pre>(((aspect adj ratio) with (via contact adj hole)) with (least greater more between range)) same ((resist photoresist photo-resist ) (photosensitive photo-sensitive (sensitive near (photo light energy radiation)) )) same ((etchstop etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon si-contain\$3 silicon-contain\$3 ) ((silicon adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion sic )))</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/20 12:28

		T		
32	9	,	USPAT;	2004/07/20 12:28
•		hole)) with (least greater more between	US-PGPUB;	
		range)) same ((resist photoresist	EPO; JPO;	
		photo-resist ) (photosensitive	DERWENT	
		photo-sensitive (sensitive near (photo light		
		energy radiation)))) same (etchstop	İ	
i		etch-stop etch adj stop hardmask hard-mask hard adj mask )		
31	108		******	
	100	hole)) with (least greater more between	USPAT;	2004/07/20 12:31
		range)) and ((resist photoresist	US-PGPUB;	
		photo-resist ) (photosensitive	EPO; JPO;	
		photo-sensitive (sensitive near (photo light	DERWENT	
		energy radiation)))) and ((etchstop		
		etch-stop etch adj stop hardmask hard-mask		
		hard adj mask ) with ((si silicon		
		si-contain\$3 silicon-contain\$3 ) ((silicon		
		adj (nitride oxynitride oxy-nitride oxy adj		
		nitride carbide)) "si.sub.3 n.sub.4" sion		
		sic )))		
33	18	(((aspect adj ratio) with (via contact adj	USPAT;	2004/07/20 10 25
		hole)) with (least greater more between	US-PGPUB;	2004/07/20 12:36
		range)) and ((resist photoresist	EPO; JPO;	
		photo-resist ) (photosensitive	DERWENT	
		photo-sensitive (sensitive near (photo light	221112112	1
		energy radiation)) )) and ((etchstop		
		etch-stop etch adj stop hardmask hard-mask		
		hard adj mask ) with ((si silicon		
		si-contain\$3 silicon-contain\$3 ) ((silicon		]
		adj (nitride oxynitride oxy-nitride oxy adj		1
		nitride carbide)) "si.sub.3 n.sub.4" sion		
		sic ))) and ((duv! (deep adj2 (uv		
		ultraviolet ultra-violet ultra adj violet))		
		) (("157" "193" "248") near (nm! nanometer		
2.4		nano-meter nano adj meter) ))		
34	90	((((aspect adj ratio) with (via contact adj	USPAT;	2004/07/20 12:36
		hole)) with (least greater more between	US-PGPUB;	
	1	range)) and ((resist photoresist	EPO; JPO;	
		photo-resist ) (photosensitive	DERWENT	
		photo-sensitive (sensitive near (photo light		
		energy radiation)))) and ((etchstop		
		etch-stop etch adj stop hardmask hard-mask hard adj mask ) with ((si silicon		
		si-contains silicon contains \ //-ili		
		si-contain\$3 silicon-contain\$3 ) ((silicon		
	1	<pre>adj (nitride oxynitride oxy-nitride oxy adj nitride carbide)) "si.sub.3 n.sub.4" sion</pre>		,
		sic )))) not ((((aspect adj ratio) with (via		İ
		contact adj hole)) with (least greater more		
		between range)) and ((resist photoresist		
		photo-resist ) (photosensitive		
		photo-sensitive (sensitive near (photo light		
		energy radiation)))) and ((etchstop		
		etch-stop etch adj stop hardmask hard-mask		
	1	hard adj mask ) with ((si silicon		
		si-contain\$3 silicon-contain\$3 ) ((silicon		
		adj (nitride oxynitride oxy-nitride oxy adj		
	1	nitride carbide)) "si.sub.3 n.sub.4" sion		
		sic ))) and ((duv! (deep adj2 (uv		
		ultraviolet ultra-violet ultra adi violet))		
		) (("157" "193" "248") near (nm! nanometer		
		nano-meter nano adj meter) )))		